

A METHOD OF FABRICATING AN SMOS FINFET

ABSTRACT OF THE DISCLOSURE

An exemplary embodiment relates to a method of FinFET channel structure formation. The method can include providing a compound semiconductor layer above an insulating layer, providing a trench in the compound semiconductor layer, and providing a strained semiconductor layer above the compound semiconductor layer and within the trench. The method can also include removing the strained semiconductor layer from above the compound semiconductor layer, thereby leaving the strained semiconductor layer within the trench and removing the compound semiconductor layer to leave the strained semiconductor layer and form the fin-shaped channel region.